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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

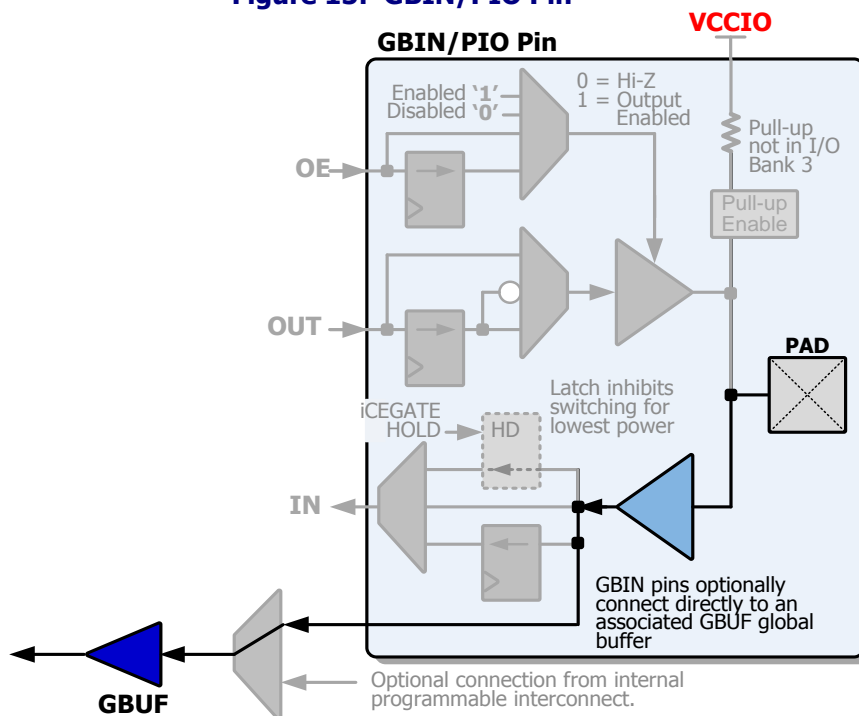
Details

Product Status	Obsolete
Number of LABs/CLBs	440
Number of Logic Elements/Cells	3520
Total RAM Bits	81920
Number of I/O	150
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	196-VFBGA, CSPBGA
Supplier Device Package	196-CSPBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/ice65l04f-tcb196c



Note the clock differences between the iCE65L04 and iCE65L08 in the CB196 package.

Figure 15: GBIN/PIO Pin



Differential Global Buffer Input

All eight global buffer inputs support single-ended I/O standards such as LVCMOS. Global buffer GBUF7 in I/O Bank 3 also provides an optional direct SubLVDS, LVDS, or LVPECL differential clock input, as shown in Figure 16. The GBIN7 and its associated differential I/O pad accept a differential clock signal. A 100 Ω termination resistor is required across the two pads. Optionally, swap the outputs from the LVDS or LVPECL clock driver to invert the clock as it enters the iCE65 device.

Figure 16: LVDS or LVPECL Clock Input

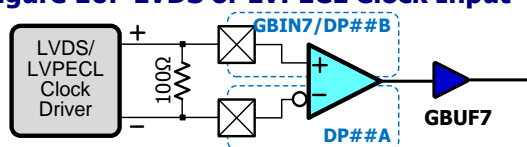


Table 15 lists the pin or ball numbers for the differential global buffer input by package style. Although this differential input is the only one that connects directly to a global buffer, other differential inputs can connect to a global buffer using general-purpose interconnect, with slightly more signal delay.

Table 15: Differential Global Buffer Input Ball/Pin Number by Package

Differential Global Buffer Input (GBIN)	I/O Bank	VQ100	CB132	'L04 CB196	'L08 CB196	CB284
GBIN7/DPxxB	3	13	N/A	G1	H3	L5
DPxxA		12	N/A	G2	H4	L3



The differential global buffer input is not available for iCE65 devices in the CB132 package. This restriction is an artifact of the pin compatibility between the CB132 and CB284 package.

Note the clock differences between the iCE65L04 and iCE65L08 in the CB196 package.

Automatic Global Buffer Insertion, Manual Insertion

The iCEcube development software automatically assigns high-fanout signals to a global buffer. However, to manually insert a global buffer input/global buffer (GBIN/GBUF) combination, use the **SB_IO_GB** primitive. To insert just a global buffer (GBUF), use the **SB_GB** primitive.

Global Hi-Z Control

The global high-impedance control signal, GHIZ, connects to all I/O pins on the iCE65 device. This GHIZ signal is automatically asserted throughout the configuration process, forcing all user-I/O pins into their high-impedance state. Similarly, the PIO pins can be forced into their high-impedance state via the JTAG controller.

Global Reset Control

The global reset control signal connects to all PLB and PIO flip-flops on the iCE65 device. The global reset signal is automatically asserted throughout the configuration process, forcing all flip-flops to their defined wake-up state. For PLB flip-flops, the wake-up state is always reset, regardless of the PLB flip-flop primitive used in the application. See [Table 3](#) for more information.

The PIO flip-flops are always reset during configuration, although the output flip-flop can be inverted before leaving the iCE65 device, as shown in [Figure 11](#).

RAM

Each iCE65 device includes multiple high-speed synchronous RAM blocks (RAM4K), each 4Kbit in size. As shown in [Table 16](#) a single iCE65 integrates between 16 to 96 such blocks. Each RAM4K block is generically a 256-word deep by 16-bit wide, two-port register file, as illustrated in [Figure 17](#). The input and output connections, to and from a RAM4K block, feed into the programmable interconnect resources.

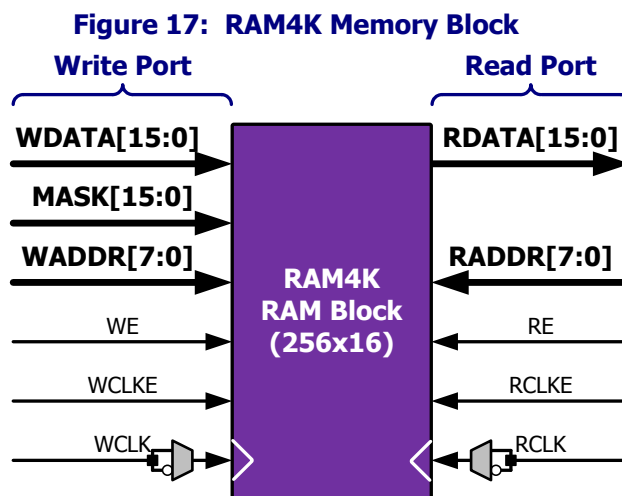


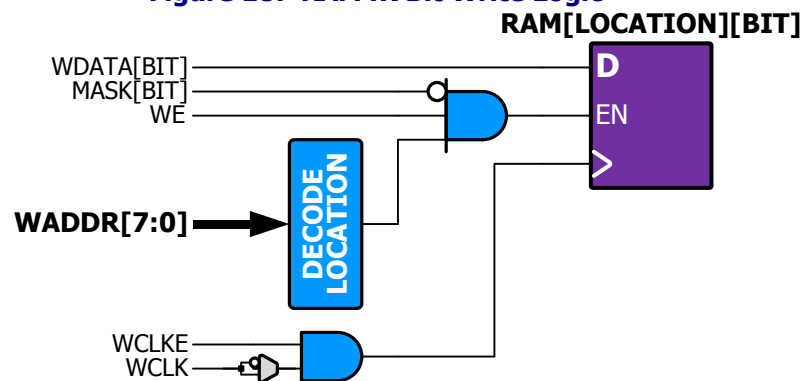
Table 16: RAM4K Blocks per Device

Device	RAM4K Blocks	Default Configuration	RAM Bits per Block	Block RAM Bits
iCE65L01	16	256 x 16	4K (4,096)	64K
iCE65L04	20			80K
iCE65L08	32			128K

Using programmable logic resources, a RAM4K block implements a variety of logic functions, each with configurable input and output data width.

- Random-access memory (RAM)
 - ◆ Single-port RAM with a common address, enable, and clock control lines
 - ◆ Two-port RAM with separate read and write control lines, address inputs, and enable

Figure 18: RAM4K Bit Write Logic



When the WCLKE signal is Low, the clock to the RAM4K block is disabled, keeping the RAM in its lowest power mode.

Table 18: RAM4K Write Operations

	WDATA[15:0]	MASK[15:0]	WADDR[7:0]	WE	WCLKE	WCLK	
Operation	Data	Mask Bit	Address	Write Enable	Clock Enable	Clock	RAM Location
Disabled	X	X	X	X	X	0	No change
Disabled					0	X	No change
Disabled	X	X	X	0	X	X	No change
Write Data	WDATA[i]	MASK[i] = 0	WADDR	1	1	↑	RAM[WADDR][i] = WDATA[i]
Masked Write	X	MASK[i] = 1	WADDR	1	1	↑	RAM[WADDR][i] = No change

To write data into the RAM4K block, perform the following operations.

- ◆ Supply a valid address on the WADDR[7:0] address input port
- ◆ Supply valid data on the WDATA[15:0] data input port
- ◆ To write or mask selected data bits, set the associated MASK input port accordingly. For example, write operations on data bit D[i] are controlled by the associated MASK[i] input.
 - MASK[i] = 0: Write operations are enabled for data line WDATA[i]
 - MASK[i] = 1: Mask write operations are disabled for data line WDATA[i]
- ◆ Enable the RAM4K write port (WE = 1)
- ◆ Enable the RAM4K write clock (WCLKE = 1)
- ◆ Apply a rising clock edge on WCLK (assuming that the clock is not inverted)

Read Operations

Figure 19 shows the logic involved in reading a location from RAM. Table 19 describes various read operations for a RAM4K block. By default, all RAM4K read operations are synchronized to the rising edge of RCLK although the clock is invertible as shown in Figure 19.

Figure 19: RAM4K Read Logic

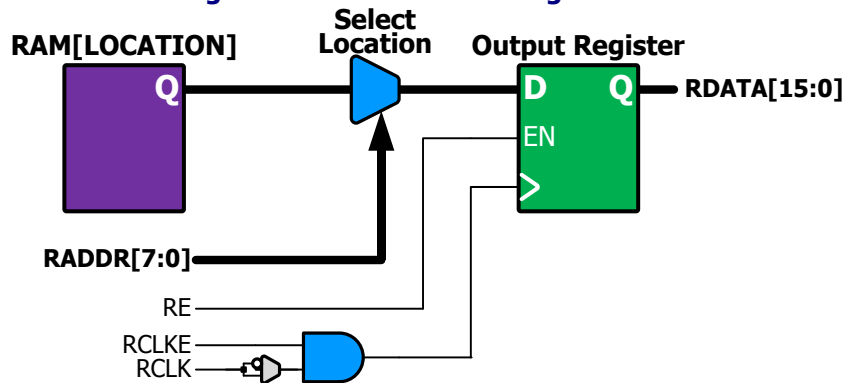


Table 19: RAM4K Read Operations

	RADDR[7:0]	RE	RCLKE	RCLK	
Operation	Address	Read Enable	Clock Enable	Clock	RDATA[15:0]
After configuration, before first valid Read Data operation	X	X	X	X	Undefined
Disabled	X	X	X	0	No Change
Disabled		X	0	X	No Change
Disabled	X	0	X	X	No change
Read Data	RADDR	1	1	↑	RAM[RADDR]

To read data from the RAM4K block, perform the following operations.

- ◆ Supply a valid address on the RADDR[7:0] address input port
- ◆ Enable the RAM4K read port (RE = 1)
- ◆ Enable the RAM4K read clock (RCLKE = 1)
- ◆ Apply a rising clock edge on RCLK
- ◆ After the clock edge, the RAM contents located at the specified address (RADDR) appear on the RDATA output port

Read Data Register Undefined Immediately after Configuration

Unlike the flip-flops in the Programmable Logic Blocks and Programmable I/O pins, the RDATA[15:0] read data output register is not automatically reset after configuration. Consequently, immediately following configuration and before the first valid Read Data operation, the initial RDATA[15:0] read value is undefined.

Pre-loading RAM Data

The data contents for a RAM4K block can be optionally pre-loaded during iCE65 configuration. If not pre-loaded during configuration, then the RAM contents must be initialized by the iCE65 application before the RAM contents are valid.

Pre-loading the RAM data in the configuration bitstream increases the size of the configuration image accordingly.

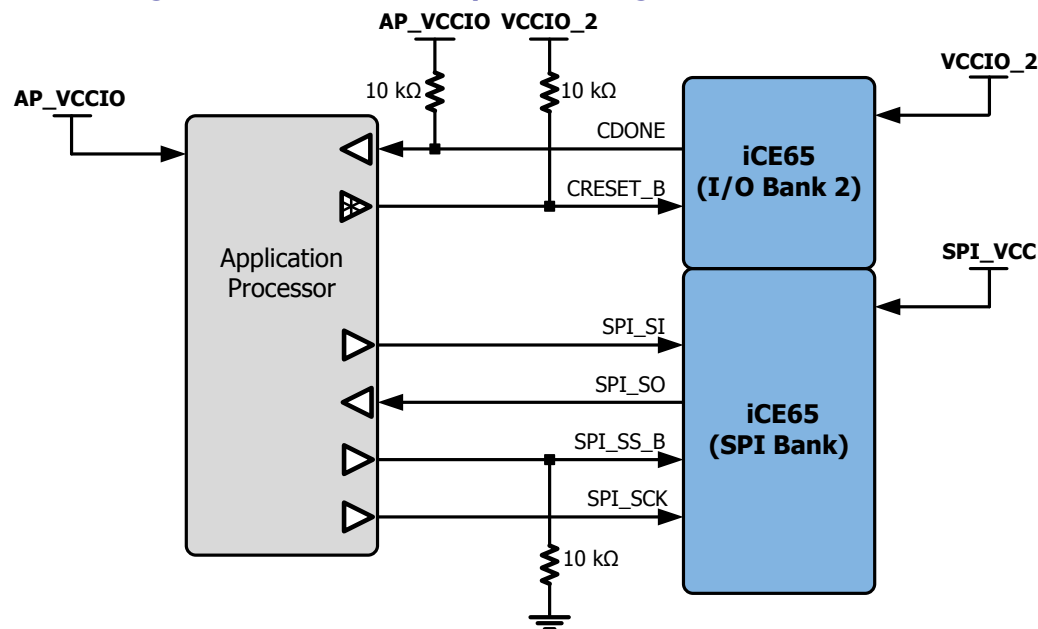
RAM Contents Preserved during Configuration

RAM contents are preserved (write protected) during configuration, assuming that voltage supplies are maintained throughout. Consequently, data can be passed between multiple iCE65 configurations by leaving it in a RAM4K block and then skipping pre-loading during the subsequent reconfiguration. See “Cold Boot Configuration Option” and “Warm Boot Configuration Option” for more information.

Low-Power Setting

To place a RAM4K block in its lowest power mode, keep WCLKE = 0 and RCLKE = 0. In other words, when not actively using a RAM4K block, disable the clock inputs.

Figure 28: iCE65 SPI Peripheral Configuration Interface



The SPI control signals are defined in [Table 25](#).

Table 29: SPI Peripheral Configuration Interface Pins (SPI_SS_B Low when CRESET_B Released)

Signal Name	Direction	iCE65 I/O Supply	Description
CDONE	AP ← iCE65	VCCIO_2	Configuration Done output from iCE65. Connect to a 10kΩ pull-up resistor to the application processor I/O voltage, AP_VCC.
CRESET_B	AP → iCE65	VCCIO_2	Configuration Reset input on iCE65. Typically driven by AP using an open-drain driver, which also requires a 10kΩ pull-up resistor to VCCIO_2.
SPI_VCC	Supply	SPI_VCC	SPI Flash PROM voltage supply input.
SPI_SI	AP → iCE65	SPI_VCC	SPI Serial Input to the iCE65 FPGA, driven by the application processor.
SPI_SO	AP ← iCE65	SPI_VCC	SPI Serial Output from CE65 device to the application processor. Not actually used during SPI peripheral mode configuration but required if the SPI interface is also used to program the NVCN.
SPI_SS_B	AP → iCE65	SPI_VCC	SPI Slave Select output from the application processor. Active Low. Optionally hold Low prior to configuration using a 10kΩ pull-down resistor to ground.
SPI_SCK	AP → iCE65	SPI_VCC	SPI Slave Clock output from the application processor.

After configuration, the SPI port pins are available to the user-application as additional PIO pins, supplied by the SPI_VCC input voltage, essentially providing a fifth “mini” I/O bank.

Enabling SPI Configuration Interface

The optional 10 kΩ pull-down resistor on the SPI_SS_B signal ensures that the iCE65 FPGA powers up in the SPI peripheral mode. Optionally, the application processor drives the SPI_SS_B pin Low when CRESET_B is released, forcing the iCE65 FPGA into SPI peripheral mode.

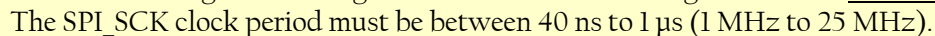
SPI Peripheral Configuration Process

[Figure 29](#) illustrates the interface timing for the SPI peripheral mode and [Figure 30](#) outlines the resulting configuration process. The actual timing specifications appear in [Table 60](#). The application processor (AP) begins by driving the iCE65 CRESET_B pin Low, resetting the iCE65 FPGA. Similarly, the AP holds the iCE65’s SPI_SS_B pin Low. The AP must hold the CRESET_B pin Low for at least 200 ns. Ultimately, the AP either releases the CRESET_B pin and allows it to float High via the 10 kΩ pull-up resistor to VCCIO_2 or drives CRESET_B High. The iCE65 FPGA enters SPI peripheral mode when the CRESET_B pin returns High while the SPI_SS_B pin is Low.

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After driving CRESET_B High or allowing it to float High, the AP must wait a minimum of t_{CR_SCK} μ s, (see [Table 60](#)) allowing the iCE65 FPGA to clear its internal configuration memory.

After waiting for the configuration memory to clear, the AP sends the configuration image generated by the iCEcube development system. An SPI peripheral mode configuration image must not use the ColdBoot or WarmBoot options. Send the entire configuration image, without interruption, serially to the iCE65's SPI_SI input on the falling edge of the SPI_SCK clock input. Once the AP sends the **0x7EAA997E** synchronization pattern, the generated SPI_SCK clock frequency must be within the specified 1 MHz to 25 MHz range (40 ns to 1 μ s clock period) while sending the configuration image. Send each byte of the configuration image with most-significant bit (msb) first. The AP sends data to the iCE65 FPGA on the falling edge of the SPI_SCK clock. The iCE65 FPGA internally captures each incoming SPI_SI data bit on the rising edge of the SPI_SCK clock. The iCE65's SPI_SO output pin is not used during SPI peripheral mode but must connect to the AP if the AP also programs the iCE65's Nonvolatile Configuration Memory (NVCM).



After sending the entire image, the iCE65 FPGA releases the CDONE output allowing it to float High via the 10 kΩ pull-up resistor to AP_VCC. If the CDONE pin remains Low, then an error occurred during configuration and the AP should handle the error accordingly for the application.

After the CDONE output pin goes High, send at least 49 additional dummy bits, effectively 49 additional SPI_SCK clock cycles measured from rising-edge to rising-edge.

After the additional SPI_CLK cycles, the SPI interface pins then become available to the user application loaded in FPGA.

To reconfigure the iCE65 FPGA or to load a different configuration image, merely restart the configuration process by pulsing CRESET_B Low or power-cycling the FPGA.

Figure 29: Application Processor Waveforms for SPI Peripheral Mode Configuration Process

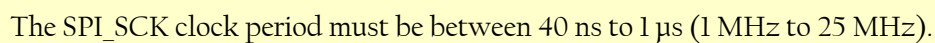
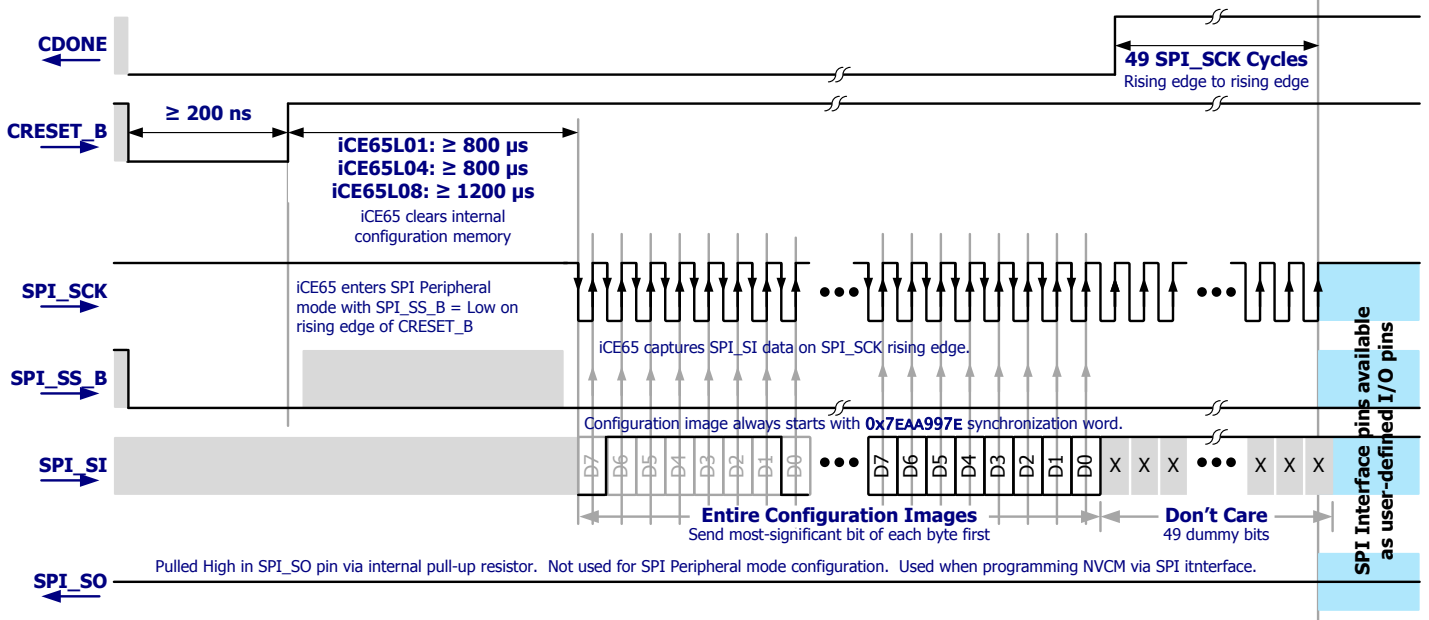


Table 31 describes how to maintain voltage compatibility for two interface scenarios. The easiest interface is when the Application Processor's (AP) I/O supply rail and the iCE65's SPI and VCCIO_2 bank supply rails all connect to the same voltage. The second scenario is when the AP's I/O supply voltage is greater than the iCE65's VCCIO_2 supply voltage.

Table 31: CRESET_B and CDONE Voltage Compatibility

Condition	CRESET_B			CDONE Pull-up	Requirement
	Direct	Open-Drain	Pull-up		
VCCIO_AP = VCC_SPI VCCIO_AP = VCCIO_2	OK	OK with pull-up	Required if using open-drain output	Recommended	AP can directly drive CRESET_B High and Low although an open-drain output recommended is if multiple devices control CRESET_B. If using an open-drain driver, the CRESET_B input must include a 10 kΩ pull-up resistor to VCCIO_2. The 10 kΩ pull-up resistor to AP_VCCIO is also recommended.
AP_VCCIO > VCCIO_2	N/A	Required, requires pull-up	Required	Required	The AP must control CRESET_B with an open-drain output, which requires a 10 kΩ pull-up resistor to VCCIO_2. The 10 kΩ pull-up resistor to AP_VCCIO is required.

JTAG Boundary Scan Port

Overview

Each iCE65 device includes an IEEE 1149.1-compatible JTAG boundary-scan port. The port supports printed-circuit board (PCB) testing and debugging. It also provides an alternate means to configure the iCE65 device.

Signal Connections

The JTAG port connections are listed in Table 32.

Table 32: iCE65 JTAG Boundary Scan Signals

Signal Name	Direction	Description
TDI	Input	Test Data Input. Must be tied off to GND when unused. (no pull-up resistor)*
TMS	Input	Test Mode Select. Must be tied off to GND when unused. (no pull-up resistor)*
TCK	Input	Test Clock. Must be tied off to GND when unused. (no pull-up resistor)*
TDO	Output	Test Data Output.
TRST_B	Input	Test Reset, active Low. Must be Low during normal device operation. Must be High to enable JTAG operations.*

* Must be tied off to GND or VCCIO_1, else VCCIO_1 draws current.

Table 33 lists the ball/pin numbers for the JTAG interface by package code. The JTAG interface is available in select package types. The JTAG port is located in I/O Bank 1 along the right edge of the iCE65 device and powered by the VCCIO_1 supply inputs. Consequently, the JTAG interface uses the associated I/O standards for I/O Bank 1.

Table 33: JTAG Interface Ball/Pin Numbers by Package

JTAG Interface	VQ100	CB132	CB196	CB284
TDI	N/A	M12	M12	T16
TMS		P14	P14	V18
TCK		L12	L12	R16
TDO		N14	N14	U18
TRST_B		M14	M14	T18

iCE65 Pin Descriptions

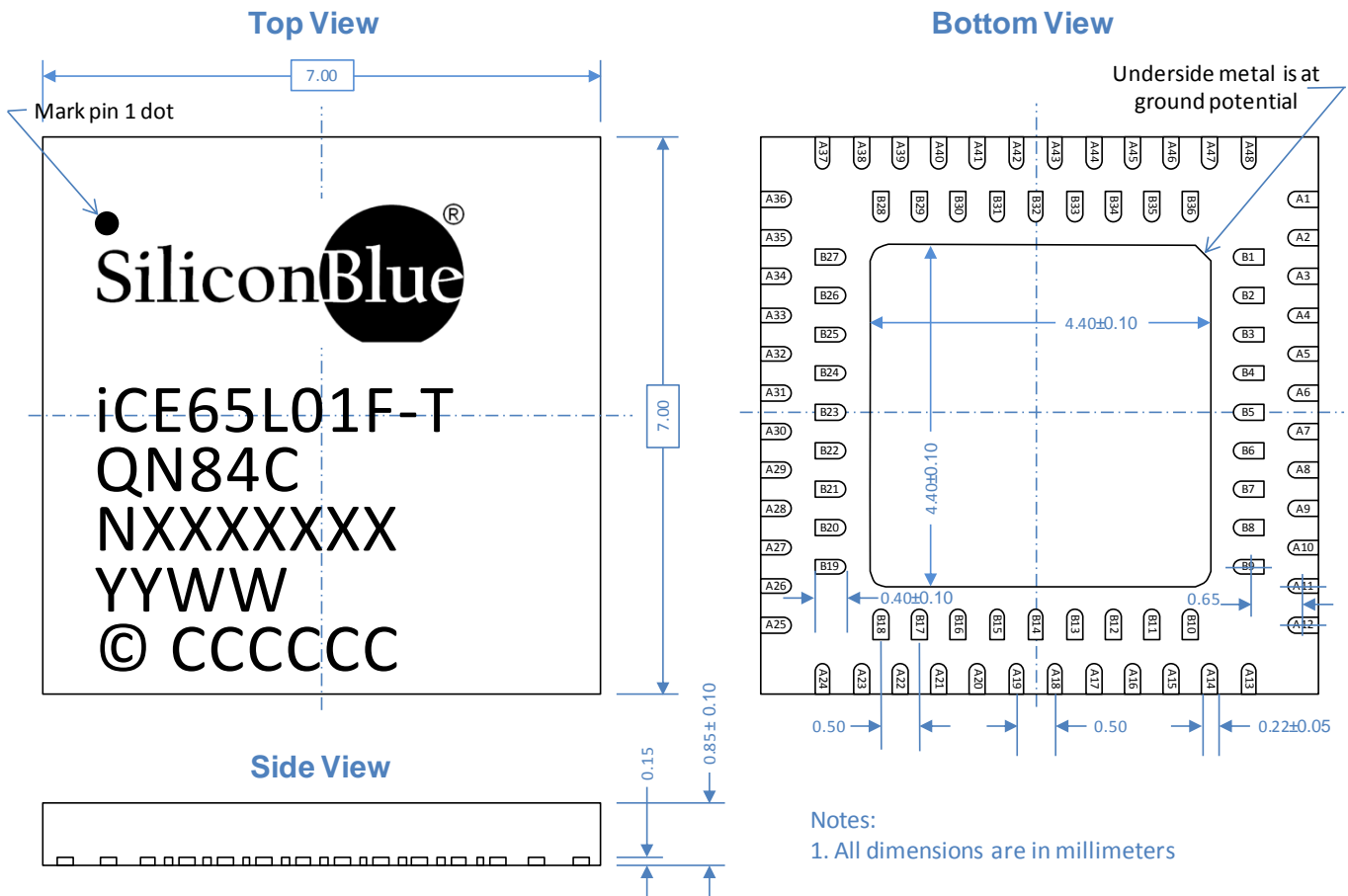
Table 36 lists the various iCE65 pins, alphabetically by name. The table indicates the directionality of the signal and the associated I/O bank. The table also indicates if the signal has an internal pull-up resistor enabled during configuration. Finally, the table describes the function of the pin.

Table 36: iCE65 Pin Description

Signal Name	Direction	I/O Bank	Pull-up during Config	Description
CDONE	Output	2	Yes	Configuration Done. Dedicated output. Includes a permanent weak pull-up resistor to VCCIO_2 . If driving external devices with CDONE output, connect a 10 kΩ pull-up resistor to VCCIO_2 .
CRESET_B	Input	2	No	Configuration Reset, active Low. Dedicated input. No internal pull-up resistor. Either actively drive externally or connect a 10 kΩ pull-up resistor to VCCIO_2 .
GBIN0/PIO0 GBIN1/PIO0	Input/IO	0	Yes	Global buffer input from I/O Bank 0. Optionally, a full-featured PIO pin.
GBIN2/PIO1 GBIN3/PIO1	Input/IO	1	Yes	Global buffer input from I/O Bank 1. Optionally, a full-featured PIO pin.
GBIN4/PIO2 GBIN5/PIO2	Input/IO	2	Yes	Global buffer input from I/O Bank 2. Optionally, a full-featured PIO pin.
GBIN6/PIO3	Input/IO	3	No	Global buffer input from I/O Bank 3. Optionally, a full-featured PIO pin.
GBIN7/PIO3	Input/IO	3	No	Global buffer input from I/O Bank 3. Optionally, a full-featured PIO pin. Optionally, a differential clock input using the associated differential input pin.
GND	Supply	All	N/A	Ground. All must be connected.
PIOx_yy	I/O	0,1,2	Yes	Programmable I/O pin defined by the iCE65 configuration bitstream. The 'x' number specifies the I/O bank number in which the I/O pin resides. The 'yy' number specifies the I/O number in that bank.
PIO2/CBSEL0	Input/IO	2	Yes	Optional ColdBoot configuration SElect input, if ColdBoot mode is enabled. A full-featured PIO pin after configuration.
PIO2/CBSEL1	Input/IO	2	Yes	Optional ColdBoot configuration SElect input, if ColdBoot mode is enabled. A full-featured PIO pin after configuration.
PIO3_yy/ DPwwz	I/O	3	No	Programmable I/O pin that is also half of a differential I/O pair. Only available in I/O Bank 3. The 'yy' number specifies the I/O number in that bank. The 'ww' number indicates the differential I/O pair. The 'z' indicates the polarity of the pin in the differential pair. 'A'=negative input. 'B'=positive input.
PIOS/SPI_SO	I/O	SPI	Yes	SPI Serial Output. A full-featured PIO pin after configuration.
PIOS /SPI_SI	I/O	SPI	Yes	SPI Serial Input. A full-featured PIO pin after configuration.
PIOS / SPI_SS_B	I/O	SPI	Yes	SPI Slave Select. Active Low. Includes an internal weak pull-up resistor to SPI_VCC during configuration. During configuration, the logic level sampled on this pin determines the configuration mode used by the iCE65 device, as shown in Figure 20 . An input when sampled at the start of configuration. An input when in SPI Peripheral configuration mode (SPI_SS_B = Low). An output when in SPI Flash configuration mode. A full-featured PIO pin after configuration.
PIOS/ SPI_SCK	I/O	SPI	Yes	SPI Slave Clock. An input when in SPI Peripheral configuration mode (SPI_SS_B = Low). An output when in SPI Flash configuration mode. A full-featured PIO pin after configuration.
TDI	Input	1	No	JTAG Test Data Input. If using the JTAG interface, use a 10kΩ pull-up resistor to VCCIO_1 . Tie off to GND when unused.

Package Mechanical Drawing

Figure 35: QN84 Package Mechanical Drawing



Top Marking Format

Line	Content	Description
1	Logo	Logo
2	iCE65L01F	Part number
	-T	Power/Speed
3	QN84C	Package type
	ENG	Engineering
4	NXXXXXXX	Lot Number
5	YYWW	Date Code
6	© CCCCCC	Country

Thermal Resistance

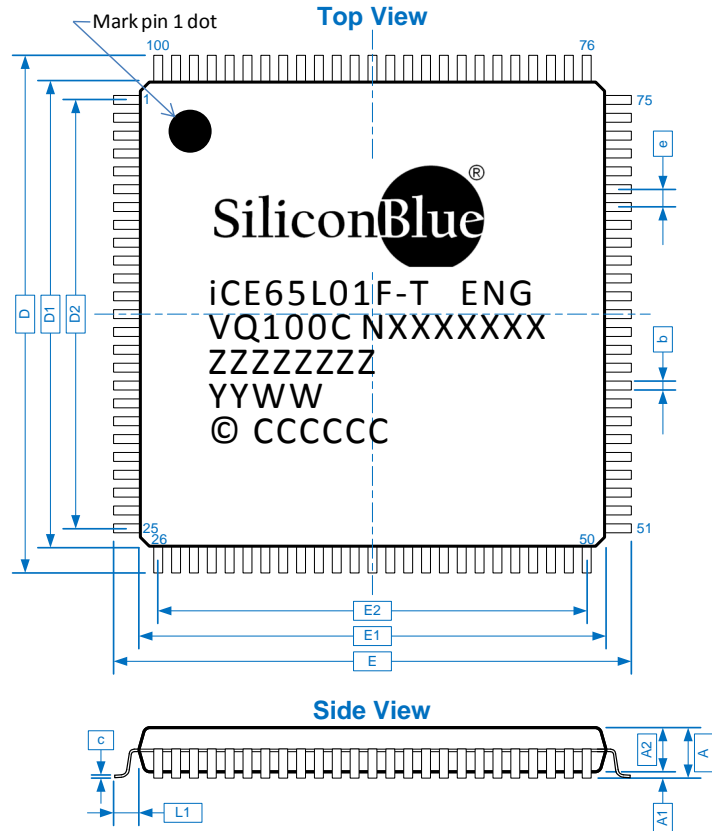
Junction-to-Ambient * θ_{JA} (°C/W)	
0 LFM	200 LFM
45	44

* With PCB thermal vias

Table 39: iCE65 VQ100 Pinout Table

Pin Function	Pin Number	Type	Bank
GBIN0/PIO0	90	GBIN	0
GBIN1/PIO0	89	GBIN	0
PIO0	78	PIO	0
PIO0	79	PIO	0
PIO0	80	PIO	0
PIO0	81	PIO	0
PIO0	82	PIO	0
PIO0	83	PIO	0
PIO0	85	PIO	0
PIO0	86	PIO	0
PIO0	87	PIO	0
PIO0	91	PIO	0
PIO0	93	PIO	0
PIO0	94	PIO	0
PIO0	95	PIO	0
PIO0	96	PIO	0
PIO0	97	PIO	0
PIO0	99	PIO	0
PIO0	100	PIO	0
VCCIO_0	88	VCCIO	0
VCCIO_0	92	VCCIO	0
GBIN2/PIO1	63	GBIN	1
GBIN3/PIO1	62	GBIN	1
PIO1	51	PIO	1
PIO1	52	PIO	1
PIO1	53	PIO	1
PIO1	54	PIO	1
PIO1	56	PIO	1
PIO1	57	PIO	1
PIO1	59	PIO	1
PIO1	60	PIO	1
PIO1	64	PIO	1
PIO1	65	PIO	1
PIO1	66	PIO	1
PIO1	68	PIO	1
PIO1	69	PIO	1
PIO1	71	PIO	1
PIO1	72	PIO	1
PIO1	73	PIO	1
PIO1	74	PIO	1
VCCIO_1	58	VCCIO	1
VCCIO_1	67	VCCIO	1
CDONE	43	CONFIG	2
CRESET_B	44	CONFIG	2
GBIN4/PIO2	iCE65L01: 33 iCE65L04: 34	GBIN	2
GBIN5/PIO2	iCE65L01: 36 iCE65L04: 33	GBIN	2
PIO2	26	PIO	2
PIO2	27	PIO	2

Figure 38: VQ100 Package Mechanical Drawing: NVCM Programmed Device Marking



Description		Symbol	Min.	Nominal	Max.	Units
Leads per Edge	X			25		Leads
	Y			25		
Number of Signal Leads		n		100		mm
Maximum Size (lead tip to lead tip)	X	E	—	16.0	—	
	Y	D	—	16.0	—	
Body Size	X	E1	—	14.0	—	
	Y	D1	—	14.0	—	
Edge Pin Center to Center	X	E2	—	12.0	—	
	Y	D2	—	12.0	—	
Lead Pitch		e	—	0.50	—	
Lead Width		b	0.17	0.20	0.27	
Total Package Height		A	—	1.20	—	
Stand Off		A1	0.05	—	0.15	
Body Thickness		A2	0.95	1.00	1.05	
Lead Length		L1	—	1.00	—	
Lead Thickness		c	0.09	—	0.20	
Coplanarity			—	0.08	—	

Top Marking Format

Line	Content	Description
1	Logo	Logo
2	iCE65L01F	Part number
	-T	Power/Speed
	ENG	Engineering
3	VQ100C	Package type and
	NXXXXXXX	Lot number
4	ZZZZZZZZ	NVCM Program. code
5	YYWW	Date Code
6	© CCCCCC	Country

Thermal Resistance

Junction-to-Ambient θ_{JA} (°C/W)	
0 LFM	200 LFM
38	32

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Ball Function	Ball Number	Pin Type	Bank
GND	K2	GND	GND
GND	K10	GND	GND
VCC	B6	VCC	VCC
VCC	F1	VCC	VCC
VCC	F11	VCC	VCC
VCC	K6	VCC	VCC
VPP_2V5	C10	VPP	VPP
VPP_FAST	A9	VPP	VPP

Ball Function	Ball Number	Pin Type	Bank
PIO0	A5	PIO	0
PIO0	A6	PIO	0
PIO0	A10	PIO	0
PIO0	A11	PIO	0
PIO0	A12	PIO	0
PIO0	B2	PIO	0
PIO0	B3	PIO	0
PIO0	B4	PIO	0
PIO0	B5	PIO	0
PIO0	B6	PIO	0
PIO0	B8	PIO	0
PIO0	B9	PIO	0
PIO0	B10	PIO	0
PIO0	B11	PIO	0
PIO0	C4	PIO	0
PIO0	C5	PIO	0
PIO0	C6	PIO	0
PIO0	C7	PIO	0
PIO0	C8	PIO	0
PIO0	C9	PIO	0
PIO0	C10	PIO	0
PIO0	C11	PIO	0
PIO0	D5	PIO	0
PIO0	D6	PIO	0
PIO0	D7	PIO	0
PIO0	D8	PIO	0
PIO0	D9	PIO	0
PIO0	D10	PIO	0
PIO0	E6	PIO	0
PIO0	E8	PIO	0
PIO0	E9	PIO	0
VCCIO_0	A8	VCCIO	0
VCCIO_0	F6	VCCIO	0
GBIN2/PIO1	F10	GBIN	1
GBIN3/PIO1	G12	GBIN	1
PIO1	B13	PIO	1
PIO1	B14	PIO	1
PIO1	C12	PIO	1
PIO1	C13	PIO	1
PIO1	C14	PIO	1
PIO1	D11	PIO	1
PIO1	D12	PIO	1
PIO1	D13	PIO	1
PIO1	D14	PIO	1
PIO1	E10	PIO	1
PIO1	E11	PIO	1
PIO1	E12	PIO	1
PIO1	E13	PIO	1
PIO1	E14	PIO	1
PIO1	F11	PIO	1
PIO1	F12	PIO	1
PIO1	F13	PIO	1

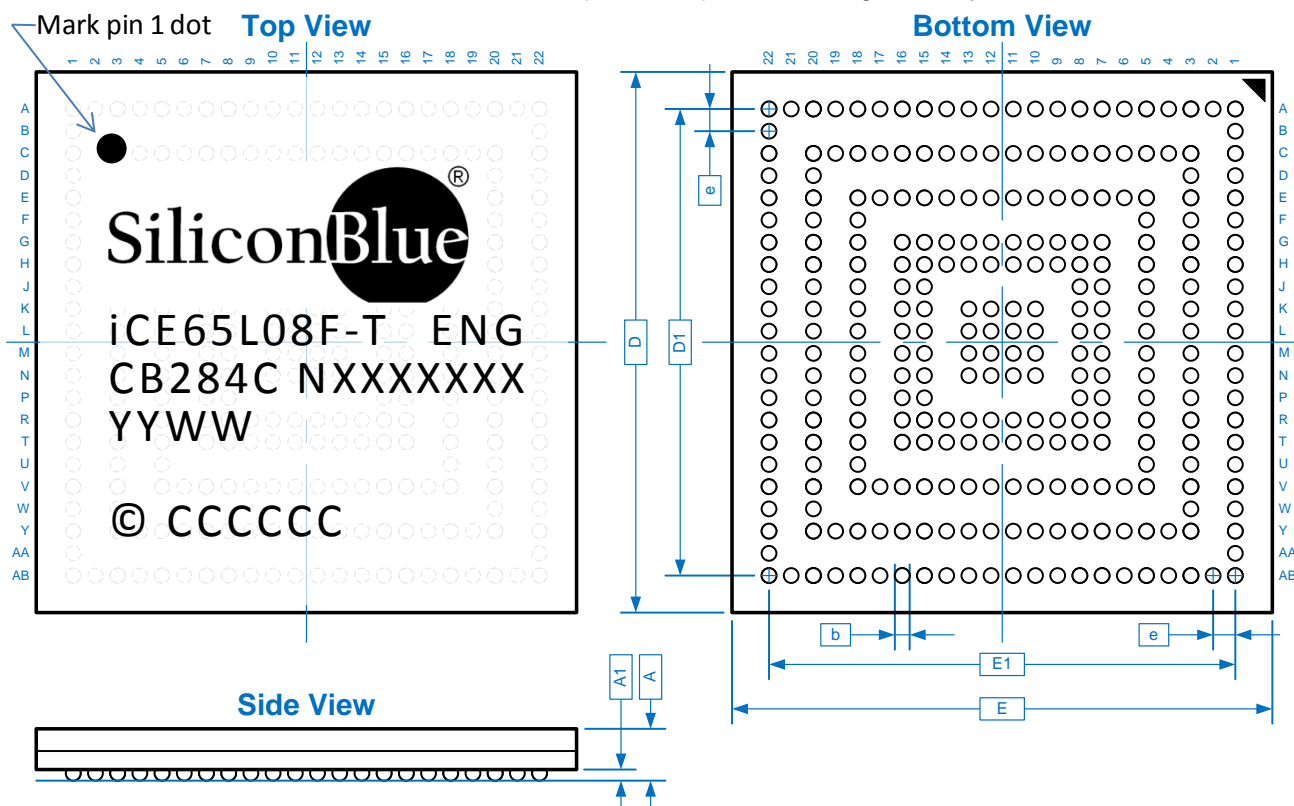
iCE65 Ultra Low-Power mobileFPGA™ Family

Ball Function	Ball Number	Pin Type by Device		Bank	CB132 Ball Equivalent
	iCE65L04 iCE65L08	iCE65L04	iCE65L08		
VCCIO_3	J7	VCCIO	VCCIO	3	E3
VCCIO_3	K3	VCCIO	VCCIO	3	—
VCCIO_3	N10	VCCIO	VCCIO	3	J6
VCCIO_3	P5	VCCIO	VCCIO	3	K1
VCCIO_3	R3	VCCIO	VCCIO	3	—
VREF	M1	VREF	VREF	3	—
PIOS/SPI_SO	T15	SPI	SPI	SPI	M11
PIOS/SPI_SI	V15	SPI	SPI	SPI	P11
PIOS/SPI_SCK	V16	SPI	SPI	SPI	P12
PIOS/SPI_SS_B	V17	SPI	SPI	SPI	P13
SPI_VCC	R15	SPI	SPI	SPI	L11
GND	C12	GND	GND	GND	—
GND	E13	GND	GND	GND	A9
GND	J3	GND	GND	GND	—
GND	K5	GND	GND	GND	F1
GND	K11	GND	GND	GND	F7
GND	L11	GND	GND	GND	G7
GND	L12	GND	GND	GND	G8
GND	L13	GND	GND	GND	G9
GND	M10	GND	GND	GND	H6
GND	M11	GND	GND	GND	H7
GND	M12	GND	GND	GND	H8
GND	N1	GND	GND	GND	—
GND	N12	GND	GND	GND	J8
GND	N18	GND	GND	GND	J14
GND	N20	GND	GND	GND	—
GND	R7	GND	GND	GND	L3
GND	T3	GND	GND	GND	—
GND	V1	GND	GND	GND	—
GND	V10	GND	GND	GND	P6
GND	Y12	GND	GND	GND	—
GND	Y16	GND	GND	GND	—
GND	AB5	GND	GND	GND	—
GND	G1	GND	GND	GND	—
GND	R1	GND	GND	GND	—
VCC	C8	VCC	VCC	VCC	—
VCC	D3	VCC	VCC	VCC	—
VCC	K12	VCC	VCC	VCC	F8
VCC	L10	VCC	VCC	VCC	G6
VCC	L20	VCC	VCC	VCC	—
VCC	M13	VCC	VCC	VCC	H9
VCC	N8	VCC	VCC	VCC	J4
VCC	N11	VCC	VCC	VCC	J7
VCC	Y8	VCC	VCC	VCC	—
VPP_2V5	E18	VPP	VPP	VPP	A14
VPP_FAST	E17	VPP	VPP	VPP	A13

Package Mechanical Drawing

Figure 49: CB284 Package Mechanical Drawing

CB284: 12 x 12 mm, 284-ball, 0.5 mm ball-pitch, chip-scale ball grid array



Description	Symbol	Min.	Nominal	Max.	Units
Number of Ball Columns	X		22		Columns
Number of Ball Rows	Y		22		Rows
Number of Signal Balls	n		284		Balls
Body Size	X	E	11.90	12.00	12.10
	Y	D	11.90	12.00	12.10
Ball Pitch	e	—	0.50	—	
Ball Diameter	b	0.27	—	0.37	
Edge Ball Center to Center	X	E1	—	10.50	—
	Y	D1	—	10.50	—
Package Height	A	—	—	1.00	
Stand Off	A1	0.16	—	0.26	

Top Marking Format

Line	Content	Description
1	Logo	Logo
2	iCE65L08F	Part number
	-T	Power/Speed
	ENG	Engineering
3	CB284C	Package type and
	NXXXXXXX	Lot number
4	YYWW	Date Code
5	N/A	Blank
6	© CCCCCC	Country

Thermal Resistance

Junction-to-Ambient θ_{JA} ($^{\circ}\text{C}/\text{W}$)	
0 LFM	200 LFM
35	28

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iCE65L08 Pad Name	Available Packages		DiePlus		
	CB196	CB284	Pad	X (μm)	Y (μm)
TDI	M12	T16	177	4,470.5	634.615
TMS	P14	V18	178	4,572.5	684.615
TCK	L12	R16	179	4,470.5	734.615
TDO	N14	U18	180	4,572.5	784.615
TRST_B	M14	T18	181	4,470.5	834.615
PIO1_00	M13	R18	182	4,572.5	884.615
PIO1_01	K11	P16	183	4,470.5	934.615
PIO1_02	L13	P15	184	4,572.5	984.615
PIO1_03	L14	P18	185	4,470.5	1,034.615
GND	G9	N18	186	4,572.5	1,084.615
GND	—	—	187	4,470.5	1,134.615
PIO1_04	J11	N16	188	4,572.5	1,184.615
PIO1_05	K12	N15	189	4,470.5	1,234.62
VCCIO_1	F9	M18	190	4,572.5	1,287.115
VCCIO_1	—	—	191	4,470.5	1,322.115
PIO1_06	J12	M15	192	4,572.5	1,357.115
PIO1_07	K14	M16	193	4,470.5	1,392.115
PIO1_08	—	T20	194	4,572.5	1,427.115
PIO1_09	—	W20	195	4,470.5	1,462.115
PIO1_10	—	V20	196	4,572.5	1,497.115
VCC	H9	M13	197	4,470.5	1,532.115
VCC	—	—	198	4,572.5	1,567.115
PIO1_11	—	R20	199	4,470.5	1,602.115
PIO1_12	—	Y22	200	4,572.5	1,637.115
PIO1_13	—	AA22	201	4,470.5	1,672.115
PIO1_14	—	U20	202	4,572.5	1,707.115
PIO1_15	J13	W22	203	4,470.5	1,742.115
PIO1_16	H11	P20	204	4,572.5	1,777.115
PIO1_17	J10	V22	205	4,470.5	1,812.115
PIO1_18	H12	U22	206	4,572.5	1,847.115
GND	K10	N20	207	4,470.5	1,882.115
GND	—	—	208	4,572.5	1,917.110
PIO1_19	H13	T22	209	4,470.5	1,952.115
PIO1_20	—	M20	210	4,572.5	1,987.115
PIO1_21	H10	R22	211	4,470.5	2,022.115
PIO1_22	—	P22	212	4,572.5	2,057.115
VCCIO_1	F9	J20	213	4,470.5	2,092.115
VCCIO_1	—	—	214	4,572.5	2,127.115
PIO1_23	G10	M22	215	4,470.5	2,162.115
PIO1_24	G11	N22	216	4,572.5	2,197.115
PIO1_25	—	K22	217	4,470.5	2,232.115
PIO1_26	—	L22	218	4,572.5	2,267.115
GBIN3/PIO1_27	G12	K18	219	4,470.5	2,302.11
GBIN2/PIO1_28	F10	L18	220	4,572.5	2,337.115
PIO1_29	—	J22	221	4,470.5	2,372.115

iCE65 Ultra Low-Power mobileFPGA™ Family

iCE65L08 Pad Name	Available Packages		DiePlus		
	CB196	CB284	Pad	X (μm)	Y (μm)
GND	F7	E13	270	3,216.98	4,054.5
GND	—	—	271	3,166.98	4,156.5
PIO0_08	D9	E15	272	3,116.98	4,054.5
PIO0_09	C10	G14	273	3,064.48	4,156.5
PIO0_10	A10	A20	274	3,029.48	4,054.5
PIO0_11	B10	H13	275	2,994.48	4,156.5
PIO0_12	—	A19	276	2,959.48	4,054.5
PIO0_13	E9	G13	277	2,924.48	4,156.5
PIO0_14	—	C16	278	2,889.48	4,054.5
PIO0_15	—	E14	279	2,854.48	4,156.5
VCCIO_0	F6	E12	280	2,819.48	4,054.5
VCCIO_0	—	—	281	2,784.48	4,156.5
PIO0_16	—	A18	282	2,749.48	4,054.5
PIO0_17	—	A17	283	2,714.48	4,156.5
PIO0_18	C9	C15	284	2,679.48	4,054.5
PIO0_19	—	A16	285	2,644.48	4,156.5
PIO0_20	B9	C14	286	2,609.48	4,054.5
PIO0_21	—	H12	287	2,574.48	4,156.5
PIO0_22	D8	A15	288	2,539.48	4,054.5
PIO0_23	C8	H11	289	2,504.48	4,156.5
PIO0_24	E8	C13	290	2,469.48	4,054.5
PIO0_25	—	A14	291	2,434.48	4,156.5
GND	B12	C12	292	2,399.48	4,054.5
GND	—	—	293	2,364.48	4,156.5
PIO0_26	B8	A13	294	2,329.48	4,054.5
PIO0_27	D7	A12	295	2,294.48	4,156.5
PIO0_28	—	C11	296	2,259.48	4,054.5
GBIN1/PIO0_29	E7	E11	297	2,224.48	4,156.5
GBIN0/PIO0_30	A7	E10	298	2,189.48	4,054.5
PIO0_31	—	G12	299	2,154.48	4,156.5
VCCIO_0	A8	A8	300	2,119.48	4,054.5
VCCIO_0	—	—	301	2,084.48	4,156.5
PIO0_32	C7	A11	302	2,049.48	4,054.5
PIO0_33	—	G11	303	2,014.48	4,156.5
PIO0_34	E6	A10	304	1,979.48	4,054.5
PIO0_35	—	C10	305	1,944.48	4,156.5
VCC	B7	C8	306	1,909.48	4,054.5
VCC	—	—	307	1,874.48	4,156.5
PIO0_36	—	A9	308	1,839.48	4,054.5
PIO0_37	A6	A7	309	1,804.48	4,156.5
PIO0_38	B6	C9	310	1,769.48	4,054.5
PIO0_39	A5	A6	311	1,734.48	4,156.5
GND	G7	K11	312	1,699.48	4,054.5
GND	—	—	313	1,664.48	4,156.5
PIO0_40	D6	E9	314	1,629.48	4,054.5
PIO0_41	C6	G10	315	1,594.48	4,156.5

I/O Characteristics

Table 49: PIO Pin Electrical Characteristics

Symbol	Description	Conditions	Minimum	Nominal	Maximum	Units
I_I	Input pin leakage current	I/O Bank 0, 1, 2 $V_{IN} = V_{CCIO_{max}}$ to 0 V			± 10	μA
		I/O Bank 3 $V_{IN} = V_{CCIO_{max}}$				
I_{OZ}	Three-state I/O pin (Hi-Z) leakage current	$V_O = V_{CCIO_{max}}$ to 0 V			± 10	μA
C_{PIO}	PIO pin input capacitance			6		pF
C_{GBIN}	GBIN global buffer pin input capacitance			6		pF
R_{PULLUP}	Internal PIO pull-up resistance during configuration	$V_{CCIO} = 3.3V$		40		k Ω
		$V_{CCIO} = 2.5V$		50		k Ω
		$V_{CCIO} = 1.8V$		90		k Ω
		$V_{CCIO} = 1.5V$				k Ω
		$V_{CCIO} = 1.2V$				k Ω
V_{HYST}	Input hysteresis	$V_{CCIO} = 1.5V$ to 3.3V		50		mV

NOTE: All characteristics are characterized and may or may not be tested on each pin on each device.

Single-ended I/O Characteristics

Table 50: I/O Characteristics (I/O Banks 0, 1, 2 and SPI only) (I/O Bank 3 iCE65L01 only)

I/O Standard	Nominal I/O Bank Supply Voltage	Input Voltage (V)		Output Voltage (V)		Output Current at Voltage (mA)	
		V_{IL}	V_{IH}	V_{OL}	V_{OH}	I_{OL}	I_{OH}
LVC MOS33	3.3V	0.80	2.00	0.4	2.40	8	8
LVC MOS25	2.5V	0.70	1.70	0.4	2.00	6	6
LVC MOS18	1.8V	35% VCCIO	65% VCCIO	0.4	1.40	4	4
LVC MOS15	1.5V	Not supported Use I/O Bank 3		0.4	1.20	2	2

Table 51: I/O Characteristics (I/O Bank 3 and iCE65L04/08 only)

I/O Standard	Supply Voltage	Input Voltage (V)		Output Voltage (V)		I/O Attribute Name	mA at Voltage
		Max. V_{IL}	Min. V_{IH}	Max. V_{OL}	Min. V_{OH}		I_{OL} , I_{OH}
LVC MOS33	3.3V	0.80	2.20	0.4	2.40	SL_LVC MOS33_8	± 8
LVC MOS25	2.5V	0.70	1.70	0.4	2.00	SB_LVC MOS25_16	± 16
						SB_LVC MOS25_12	± 12
						SB_LVC MOS25_8 *	± 8
						SB_LVC MOS25_4	± 4
LVC MOS18	1.8V	35% VCCIO	65% VCCIO	0.4	VCCIO-0.45	SB_LVC MOS18_10	± 10
						SB_LVC MOS18_8	± 8
						SB_LVC MOS18_4 *	± 4
						SB_LVC MOS18_2	± 2
LVC MOS15	1.5V	35% VCCIO	65% VCCIO	25% VCCIO	75% VCCIO	SB_LVC MOS15_4	± 4
						SB_LVC MOS15_2 *	± 2
MDDR	1.8V	35% VCCIO	65% VCCIO	0.4	VCCIO-0.45	SB_MDDR10	± 10
						SB_MDDR8	± 8
						SB_MDDR4 *	± 4
						SB_MDDR2	± 2
SSTL2 (Class 2)	2.5V	VREF-0.180	VREF+0.180	0.35	VTT+0.430	SB_SSTL2_CLASS_2	± 16.2
SSTL2 (Class 1)				0.54		SB_SSTL2_CLASS_1	± 8.1
SSTL18 (Full)	1.8V	VREF-0.125	VREF+0.125	0.28	VTT+0.280	SB_SSTL18_FULL	± 13.4
SSTL18 (Half)				VTT-0.475	VTT+0.475	SB_SSTL18_HALF	± 6.7

NOTES:

SSTL2 and SSTL18 I/O standards require the VREF input pin, which is only available on the CB284 package and die-based products.

		minimum temperature to –40°C in Figure 2 and Table 48 . Added NVCM programming temperature to Table 48 .
1.3	17-DEC-2008	Added footprint and pinout information for the CS110 Wafer-Level Chip-Scale Ball Grid Array. Clarified that the CB196 footprint shown is for the iCE65L04; the iCE65L08 footprint for the CB196 package is similar but different. Added updated information on Differential Inputs and Outputs , including support for SubLVDS. Updated Electrical Characteristics and AC Timing Guidelines sections. Added support for the LVCMOS15 I/O standard. Corrected the diagram showing the direct differential clock input, Figure 16 . Updated the number of I/Os by package in Table 34 . Updated company address. Other minor updates throughout.
1.2	11-OCT-2008	Updated I/O Bank 3 characteristics in Table 7 and Table 51 . Corrected label in Figure 14 . Added JTAG configuration to Table 20 . Added pull-up resistor information in Table 22 and Figure 21 . Added “ Internal Device Reset ” section. Updated internal oscillator performance in and Table 57 . Updated configuration timing in Table 58 based on new oscillator timing. Completely reorganized the “ Package and Pinout Information ” section. Added information on CS63 and CB196 packages. Updated information on VPP_2V5 signal in Table 36 . Reduced package height for CB132 and CB284 packages to 1.0 mm. Added “ Differential Inputs ” and “ Differential Outputs ” sections.
1.1	4-SEPT-2008	Updated package roadmap (Table 2) and updated ordering codes (Figure 2). Updated Figure 7 . Updated Figure 24 . Added CS63 package footprint (Figure 36), pinout (Table 39) and Package.
1.0	31-MAY-2008	Initial public release.